

Ch.9: Phosphorescence in OLEDs

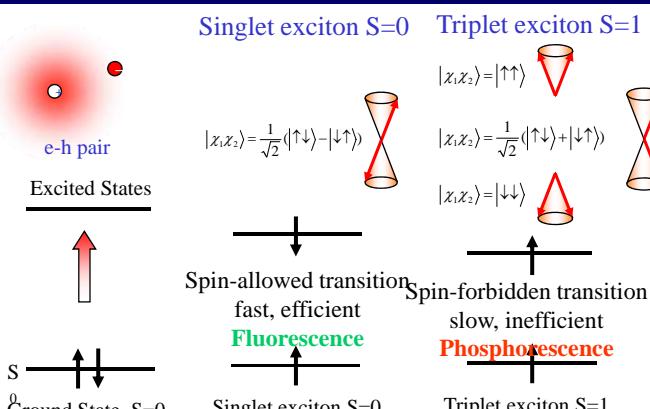
M. Baldo and M. Segal, phys. stat. sol. (a) **201**, 1205 (2004)

2009. 5. 2.

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Relaxation of Singlet & Triplet Excitons



Fluorescence : Radiation restricted to singlet excitons, $\rightarrow \eta \sim 25\%$
Phosphorescence : Radiation is from triplets $\rightarrow \eta \sim 100\%$.

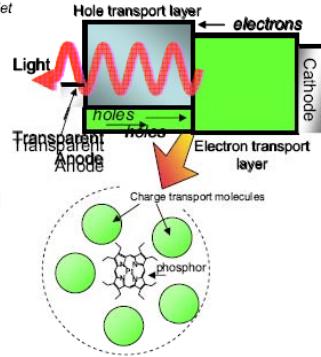
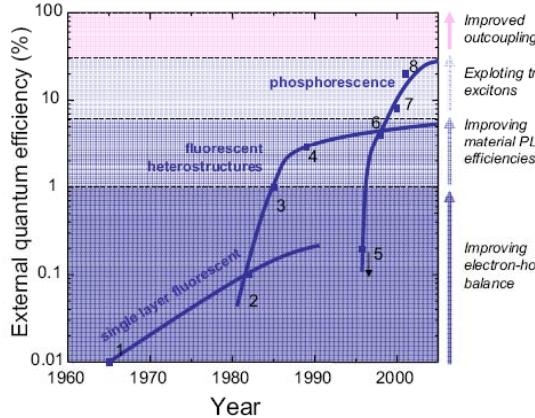
If the excited state is formed from the combination of two uncorrelated electrons, then in a completely random formation process the relative degeneracies of the singlet and triplet states result in a 1:3 singlet : triplet ratio, i.e. the fraction of singlet excitons is $\chi_s = 0.25$.

M. Baldo and M. Segal, phys. stat. sol. (a) **201**, 1205 (2004)



QE of OLEDs and a brief history

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1. Helfrich & Schneider, PRL, **14**, 229 (1965), 2. Vincett, et al. Thin Solid Films, **94**, 171 (1982)
3. Tang & Van Slyke, APL, **11**, 913 (1987), 4. Tang, Van Slyke & Chen, JAP, **65**, 3610, (1989)
5. Hoshino & Suzuki, APL, **69**, 224 (1996), 6. Baldo, et al, Nature, **395**, 151, (1998), 7. Baldo, et al, APL, **75**, 4, (1999),
8. Adachi, et al, JAP, **90**, 5048, (2001)

M. Baldo, IMID/IDMC '06 DIGEST, 645-674 (2006)

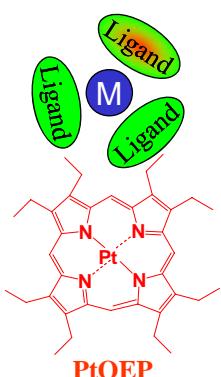
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Organic Phosphorescent Dyes

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Ligand-centered
Exciton (LC)



Triplet lifetime $\tau \sim 100 \mu\text{s}$

^1LC

IC

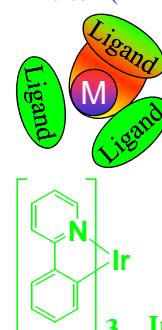
^3LC

ISC

$^1\text{MLCT}$

Ground state
 S_0

Metal-Ligand Charge Transfer
Exciton (MLCT)



Triplet lifetime $\tau \sim 1 \mu\text{s}$

$$H_{\text{SO}} = \frac{Ze^2}{2m^2c^2} \frac{1}{r^3} \vec{L} \cdot \vec{S} \propto Z^4$$

- The emissive state is a mixture of a LC exciton and a MLCT exciton
- The MLCT state has stronger singlet - triplet mixing, due to the overlap with the heavy metal atom.
- For strong spin-orbit coupling, the IC and ISC rates are very fast.

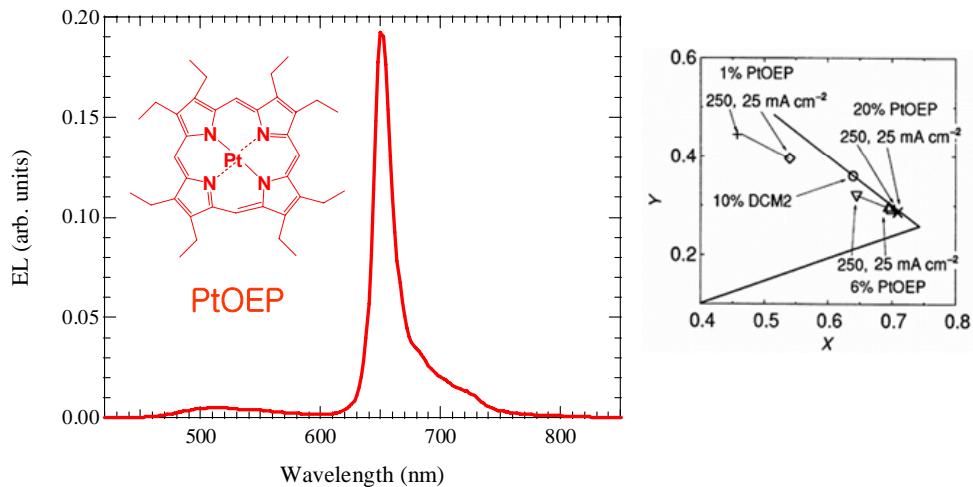


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Phosphorescent Dye OLED

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M. A. Baldo, et al, Nature 395, 151 (1998)

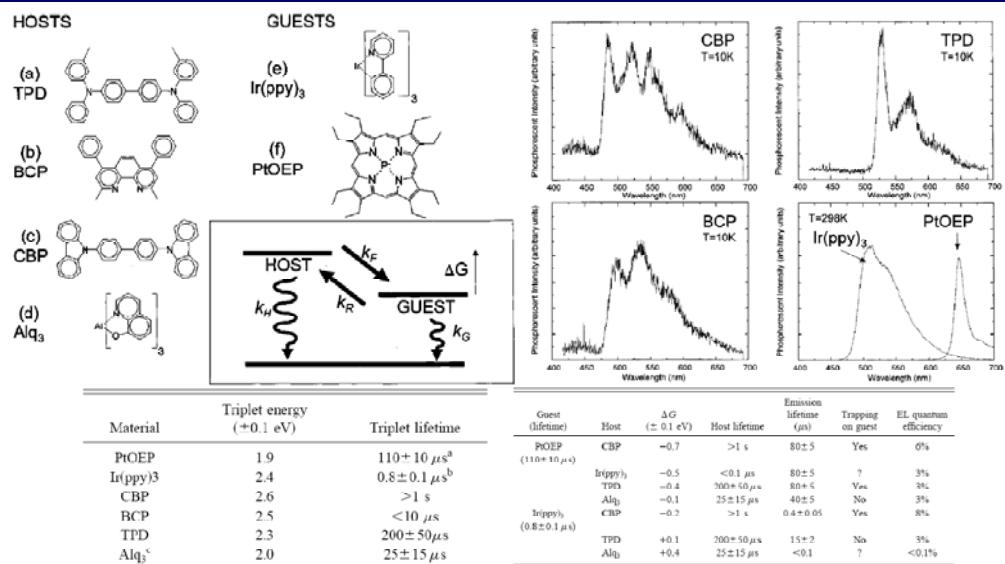


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Triplet energy of R & G phosphors

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M. A. Baldo and S. R. Forrest, Phys. Rev. B 62, 10958–10966 (2000).



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Triplet energy of a blue phosphor and its hosts

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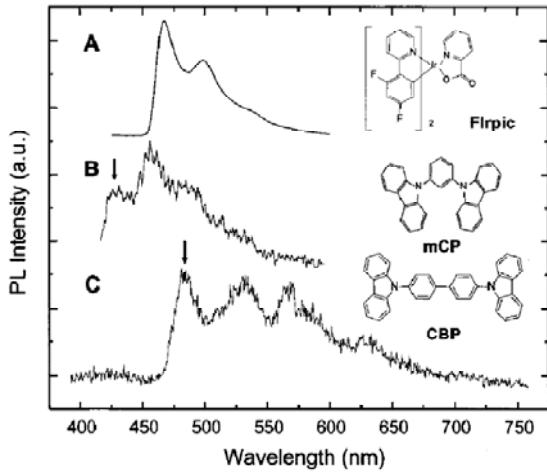
Firpic = iridium(III)bis[(4,6-difluorophenyl)-pyridinato-N,C^{2'}]picolinate, $E_t=2.65$ eV

Host

4,4'-N,N'-dicarbazole-biphenyl (CBP),
 $E_t=2.56$ eV, a maximum EQE= 5.7%
C. Adachi, R. C. Kwong, P. Djurovich, V. Adamovich, M. A. Baldo, M. E. Thompson, and S. R. Forrest, Appl. Phys. Lett. 79, 2082 (2001)

3,5'-N,N'-dicarbazole-benzene (mCP),
 $E_t=2.9$ eV, EQE=7.5%
R. J. Holmes, S. R. Forrest, Y. J. Tung, R. C. Kwong, J. J. Brown, S. Garon, and M. E. Thompson, Appl. Phys. Lett. 82, 2422 (2003).

4,4'-bis(9-dicarbazolyl)-2,2'-dimethyl-biphenyl (CDBP), $E_t=3.0$ eV, EQE=10%
S. Tokito, T. Iijima, Y. Suzuri, H. Kita, T. Tsuzuki, and F. Saito, Appl. Phys. Lett. 83, 569 (2003).



R. J. Holmes, S. R. Forrest, Y. J. Tung, R. C. Kwong, J. J. Brown, S. Garon, and M. E. Thompson, Appl. Phys. Lett. 82, 2422 (2003).

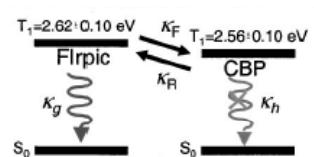
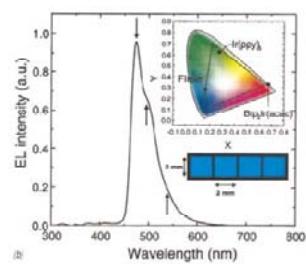
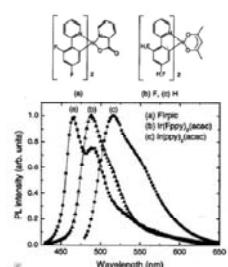


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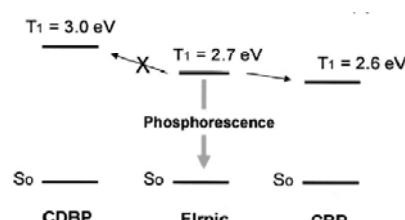
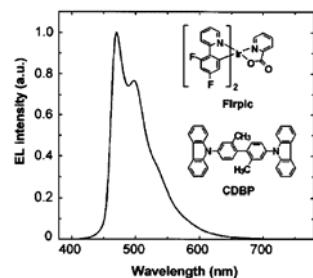
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Blue phosphorescent OLED

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C. Adachi, R. C. Kwong, P. Djurovich, V. Adamovich, M. A. Baldo, M. E. Thompson, and S. R. Forrest, Appl. Phys. Lett. 79, 2082 (2001)



S. Tokito, T. Iijima, Y. Suzuri, H. Kita, T. Tsuzuki, and F. Saito, Appl. Phys. Lett. 83, 569 (2003).



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Host and Phosphorescent Dopant Materials

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	Blue	Green	Red
Dopant	<p>FIrpic $(CF_3ppy)_2Ir(pic)$</p>	<p>Ir(ppy)₃ Ir(ppy)₂acac Ir(mpp)₃</p>	<p>Btp₂Ir(acac) PtOEP</p>
Host	<p>CBP mCP</p>	<p>UGH2 PVK</p>	<p>TAZ CN-PPV</p>
Hole/Exciton Blocking Materials	<p>BCP</p>	<p>BAiq</p>	<p>C₆₀F₄₂</p>

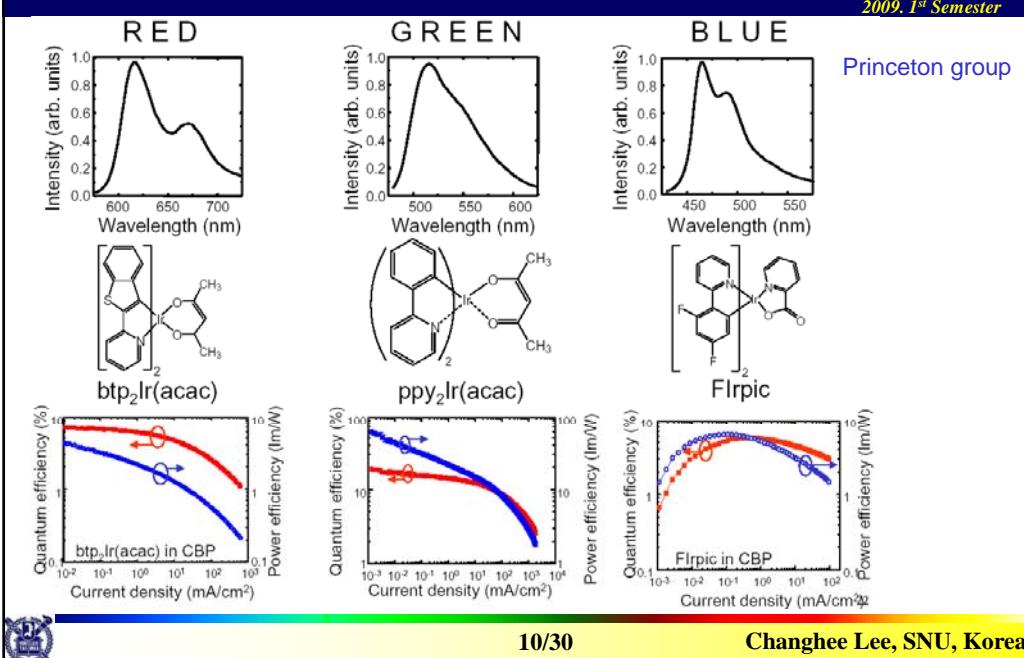
Dr. H. N. Cho (InkTek)

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Organic Electrophosphorescence devices

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Energy transfer in blue phosphorescent OLEDs

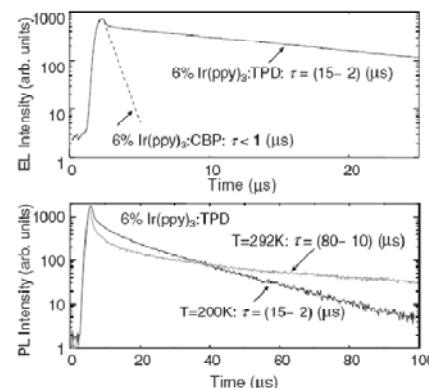
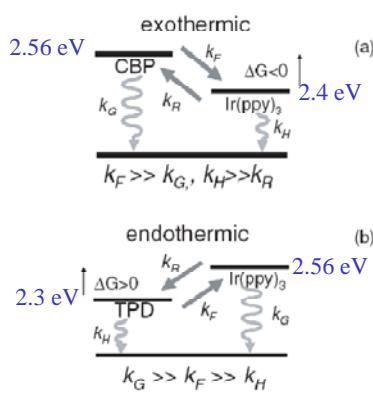
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- endothermic energy transfer
- exothermic energy transfer
- charge trapping



Exothermic and endothermic energy transfer

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Slow endothermic energy transfer from TPD to Ir(ppy)₃

Fig. 5 a) The electroluminescent response of the endothermic system Ir(ppy)₃:TPD, as compared to the exothermic system Ir(ppy)₃:CBP. The lifetime of Ir(ppy)₃ in a TPD host is significantly longer (15 μs) than the natural radiative lifetime of Ir(ppy)₃ (<1 μs). The initial peak in the response is principally due to fluorescence from TPD. (b) The photoluminescent response of 8% Ir(ppy)₃ in TPD at $T = 292\text{ K}$ and $T = 200\text{ K}$. The lifetime increases at low temperatures, consistent with a thermally activated process such as endothermic energy transfer. However, unlike the EL response, the initial transient in the photoluminescent response is comprised entirely of emission from photo-excited Ir(ppy)₃. Adapted from Ref. [24].



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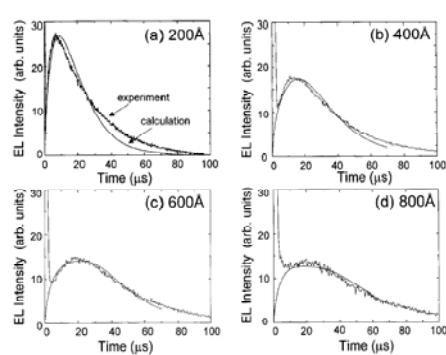
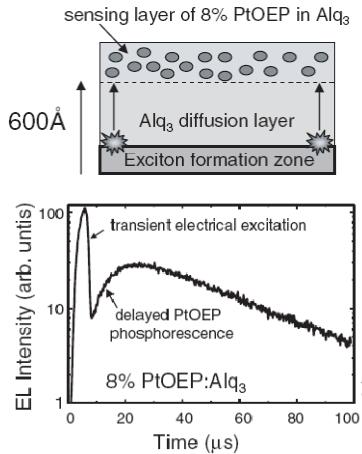


FIG. 6. The normalized phosphorescent transients for PtOEP in Alq₃ recorded at 650 nm for diffusion distances of (a) 200 Å, (b) 400 Å, (c) 600 Å, and (d) 800 Å. Also shown are the calculated transients (smooth curves) based on nondispersive diffusion of triplets given a diffusion coefficient of $D = (8 \pm 5) \times 10^{-8}$ cm²/s, and a triplet exciton lifetime in Alq₃ of $\tau = 25 \pm 15$ μs.

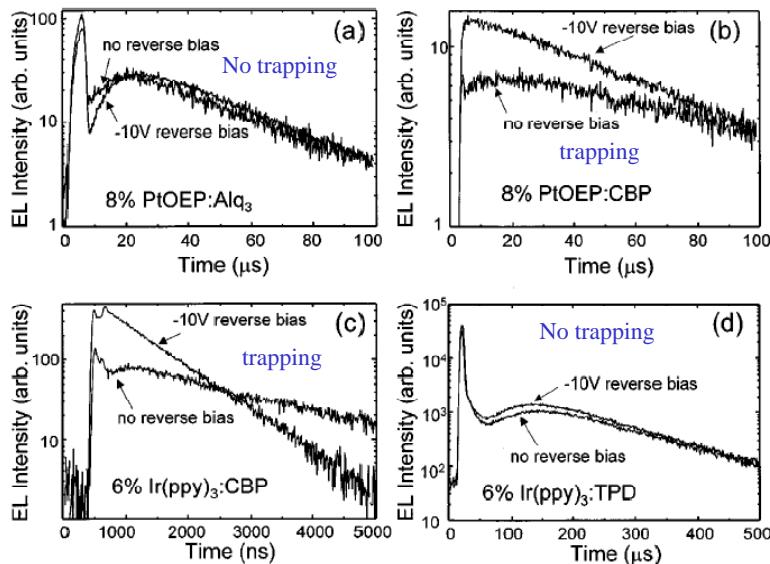
The delay in the PtOEP phosphorescence after an electrical excitation pulse is due to triplet diffusion through the Alq₃ host. The delay is observed to decrease to zero as the exciton formation zone is moved closer to the PtOEP layer, confirming that excitons are formed initially in the Alq₃ host. These experiments were used to estimate the triplet exciton lifetime in Alq₃ to be (25 ± 15) μs.

M. Baldo and M. Segal, phys. stat. sol. (a) **201**, 1205 (2004); M. A. Baldo and S. R. Forrest, Phys. Rev. B **62**, 10958–10966 (2000).



Charge trapping

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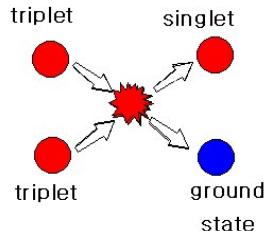
M. A. Baldo and S. R. Forrest, Phys. Rev. B **62**, 10958–10966 (2000).



Quantum Efficiency vs Current

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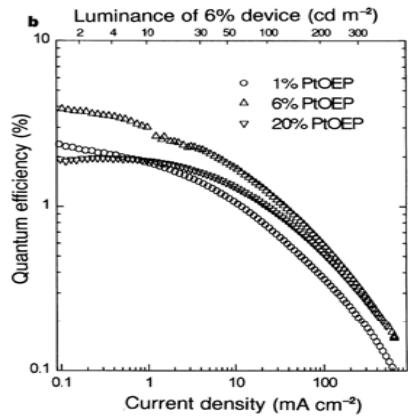
Triplet – Triplet (T – T) Annihilation



Q.E. decay as current is increased is due to

T-T annihilation

- decrease the effects of T-T annihilation by:
 - short triplet lifetime will decrease T-T annihilation
 - decrease dopant aggregation in the thin film



Ref. M. A. Baldo, C. Adachi, and S. R. Forrest, Phys. Rev. B **62**, 10967 (2000)



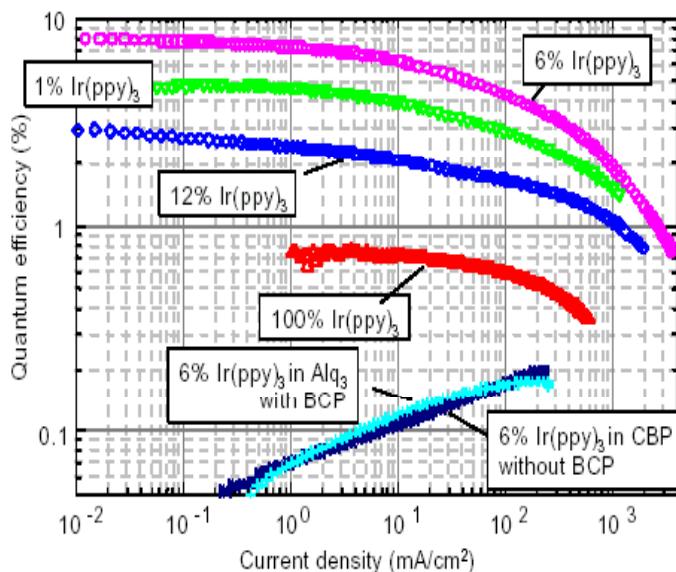
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Reduced Efficiency Roll-off with Short Triplet Exciton Lifetime

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Ir(ppy)_3
triplet exciton τ :
 $\sim 500\text{ns}$ (doped in
CBP)

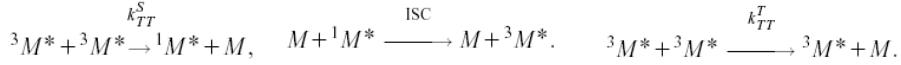


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Triplet – Triplet (T – T) Annihilation

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Rate equation for the triplet-triplet annihilation

$$\frac{dn_T}{dt} = -\frac{n_T}{\tau} - k_T n_T^2 + \frac{J}{qd}$$

1) transient $t > 0, J(t) = 0$

i) $k_T n_T(0) \ll \frac{1}{\tau}$ $n_T \approx n_T(0)e^{-\frac{t}{\tau}}$

ii) $k_T n_T(0) \gg \frac{1}{\tau}$ $\frac{dn_T}{dt} \approx -k_T n_T^2$

$$n_T \approx \frac{1}{At + B} \quad \frac{-A}{(At + B)^2} \approx \frac{-k_T}{(At + B)^2} \quad \therefore A = k_T, B = \frac{1}{n_T(0)}$$

$$\therefore n_T \approx \frac{1}{At + B} = \frac{1}{k_T t + \frac{1}{n_T(0)}} = \frac{n_T(0)}{1 + n_T(0)k_T t}$$



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Transient Solution

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trial solution

$$n_T(t) = \frac{1}{Ae^{\frac{t}{\tau}} + B} \quad \frac{-\frac{A}{\tau}e^{\frac{t}{\tau}}}{(Ae^{\frac{t}{\tau}} + B)^2} = -\frac{\frac{1}{\tau}}{(Ae^{\frac{t}{\tau}} + B)} - \frac{k_T}{(Ae^{\frac{t}{\tau}} + B)^2}$$

$$-\frac{A}{\tau}e^{\frac{t}{\tau}} = -\frac{1}{\tau}(Ae^{\frac{t}{\tau}} + B) - k_T \quad \therefore B = -k_T \tau$$

$$t = 0 ; n_T(0) = \frac{1}{A + B} \quad \therefore A = \frac{1}{n_T(0)} - B = \frac{1}{n_T(0)} + k_T \tau$$

$$\therefore n_T(t) = \frac{n_T(0)}{[1 + k_T \tau n_T(0)]e^{\frac{t}{\tau}} - k_T \tau n_T(0)}$$

$$\text{Light emission intensity} \quad L(t) = \frac{n_T(t)}{\tau} = \frac{L(0)}{(1 + K\tau)e^{\frac{t}{\tau}} - K\tau} \quad (\text{let } k_T n_T(0) = K)$$

M. A. Baldo, C. Adachi, and S. R. Forrest, Phys. Rev. B **62**, 10967 (2000)

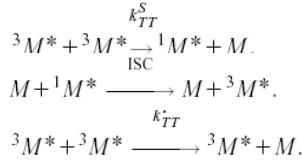


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T – T Annihilation: Transient behavior

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Rate equation for the T-T annihilation

$$\frac{dn_T}{dt} = -\frac{n_T}{\tau} - k_T n_T^2 + \frac{J}{qd}$$

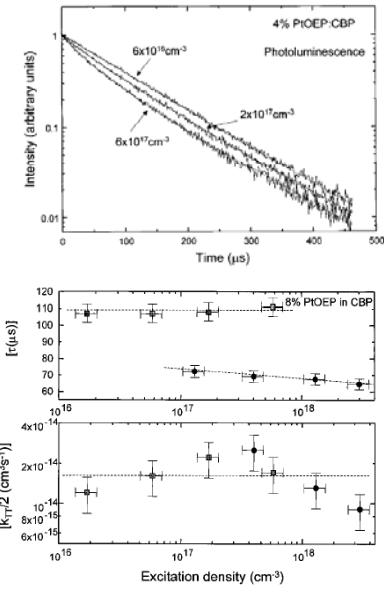
Transient behavior: J=0

$$[{}^3M^*(t)] = \frac{[{}^3M^*(0)]}{\left(1 + [{}^3M^*(0)] \frac{k_{TT}\tau}{2}\right) e^{t/\tau} - [{}^3M^*(0)] \frac{k_{TT}\tau}{2}}$$

$$K = \frac{1}{2} k_{TT} [{}^3M^*(0)].$$

$$L(t) = \frac{L(0)}{(1 + K\tau e^{t/\tau} - K\tau)},$$

M. A. Baldo, C. Adachi, and S. R. Forrest, Phys. Rev. B **62**, 10967 (2000)



T – T Annihilation: Steady-state solution

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$$\frac{dn_T}{dt} = 0 \quad k_T n_T^2 + \frac{n_T}{\tau} - \frac{J}{qd} = 0$$

(근의 공식)

$$n_T = \frac{-\frac{1}{\tau} + \sqrt{\left(\frac{1}{\tau}\right)^2 + \frac{4Jk_T}{qd}}}{2k_T} = \frac{1}{2k_T\tau} \left[-1 + \sqrt{1 + \frac{4Jk_T\tau^2}{qd}} \right] = \frac{1}{2k_T\tau} \left[-1 + \sqrt{1 + \frac{8J}{J_T}} \right] \quad (\because \frac{k_T\tau^2}{2qd} = J_T^{-1})$$

$$\text{Light emission intensity} \quad L = \frac{n_T}{\tau} \quad \text{QE : } \eta = \frac{L}{J} = \frac{n_T}{J\tau}$$

$$\eta_0 : k_T = 0 \quad \text{인 경우, 즉, T-T annihilation이 없는 경우이므로} \quad \frac{n_T}{\tau} = \frac{J}{qd}$$

$$\therefore \eta_0 = \frac{L}{J} = \frac{\frac{n_T}{\tau}}{J} = \frac{1}{qd}$$

$$\frac{\eta}{\eta_0} = \frac{qd}{2k_T\tau^2 J} \left[-1 + \sqrt{1 + \frac{8J}{J_T}} \right] = \frac{J_T}{4J} \left[-1 + \sqrt{1 + \frac{8J}{J_T}} \right]$$

M. A. Baldo, C. Adachi, and S. R. Forrest, Phys. Rev. B **62**, 10967 (2000)



Efficiency Roll-off

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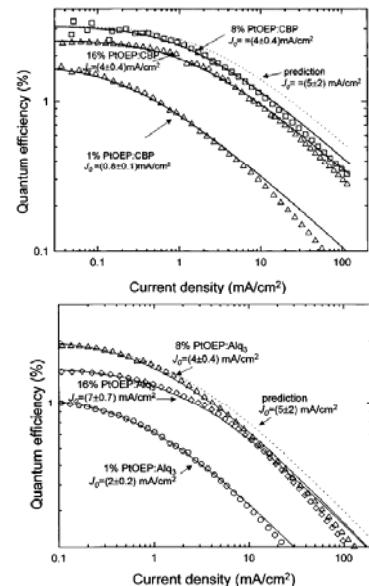
Steady-State: $d[{}^3M]/dt=0$

$$\frac{\eta}{\eta_0} = \frac{J_0}{4J} \left(\sqrt{1 + 8 \frac{J}{J_0}} - 1 \right), \quad J_0 = \frac{4qd}{k_{TT}\tau^2}$$

current density required to excite every phosphorescent molecule (i.e., the onset of saturation) $J_s = \frac{[M]qd}{\tau}$,

TABLE I. Current densities at the onset of $T-T$ annihilation (J_0) as compared to predictions based on transient decays, and the estimated current density required to saturate the phorphors.

	1% PtOEP in CBP	1% PtOEP in Alq ₃	8% PtOEP in CBP	8% PtOEP in Alq ₃	16% PtOEP in CBP	16% PtOEP in Alq ₃
J_0 from steady-state response (mA/cm ²)	0.8 ± 0.1	2.4 ± 0.2	4.4 ± 0.4	3.8 ± 0.4	4.4 ± 0.4	7.4 ± 0.7
J_0 from transient response (mA/cm ²)	7 ± 2	8 ± 3	5 ± 2	5 ± 2	4 ± 1	6 ± 2
Saturation threshold current density (mA/cm ²)	40 ± 20	200 ± 100	400 ± 80	800 ± 200	800 ± 200	1000 ± 300



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Triplet-polaron annihilation

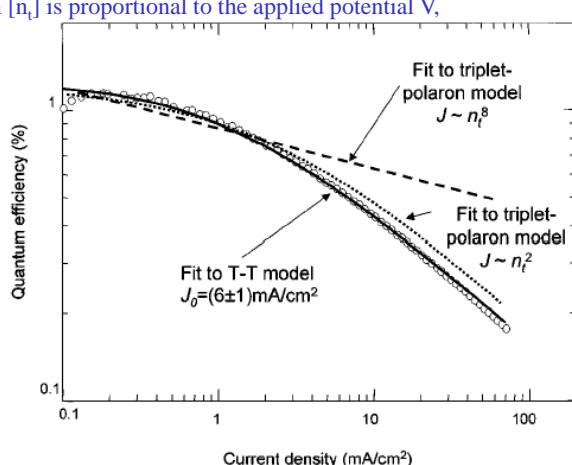
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$$\frac{d[{}^3M^*]}{dt} = - \frac{[{}^3M^*]}{\tau} - k_e [{}^3M^*][n_t] + \frac{J}{qd},$$

Assuming bulk limited transport, then $[n_t]$ is proportional to the applied potential V ,

$$\frac{\eta}{\eta_0} = \frac{1}{1 + \alpha V},$$

$$J \propto V^{l+1}$$



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Triplet-polaron annihilation

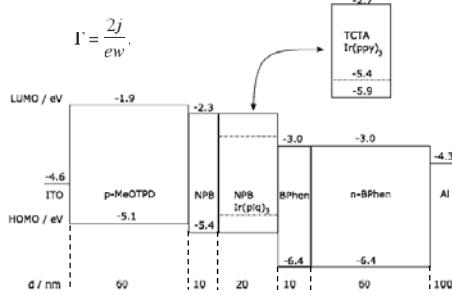
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$$\frac{d[n_{ex}]}{dt} = -\frac{[n_{ex}]}{\tau} - \frac{1}{2}k_{TT}[n_{ex}]^2 - k_p \left[\frac{\rho_c(j)}{e} \right] [n_{ex}] + \frac{j}{ew}$$

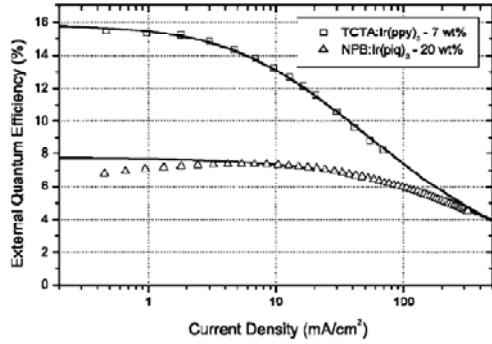
$$\frac{\eta(j)}{\eta_0} = \Theta \left[\sqrt{\frac{\Delta^2 + \Gamma k_{TT}}{k_{TT}^2} - \frac{\Delta}{k_{TT}}} \right]$$

$$\Theta = \frac{ew}{\tau j},$$

$$\Delta = \Delta(k_p) = \left(\frac{1}{\tau} + k_p C j^{1/(l+1)} \right)$$



	τ [μs]	k_{TT} [10 ⁻¹² cm ³ s ⁻¹]	$k_{p,e}$ [10 ⁻¹² cm ³ s ⁻¹]	$k_{p,h}$ [10 ⁻¹² cm ³ s ⁻¹]	η_0 [%]	w [nm]
TCTA:Ir(ppy) ₃	(1.58±0.05)	(3±2)	(0.2±0.1)	(0.3±0.2)	15.8	10
NPB:Ir(piq) ₃	(1.10±0.05)	(1.4±0.6)	(0.7±0.2)	(0.2±0.2)	7.6	19



S. Reineke, K. Walzer, and K. Leo, Phys. Rev. B 75, 125328 (2007)



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